

Amendments to the Claims

Claims 1-10 (*Cancelled*)

11. (New) A Silicon on Insulator (SOI) device, comprising:
 - at least one isolating layer made of a dielectric material
 - at least one silicon substrate arranged on said isolating layer and having a buried passivation layer, which is in particular oxide-based;
 - at least one component integrated in the silicon substrate, which component has at least one slightly doped zone, and is a lateral transistor, as well as
 - at least a first, in particular planar, metallization region arranged between the isolating layer and the component, and
 - at least a second, in particular planar, metallization region arranged on the side of the silicon substrate facing away from the isolating layer, in the area of the component, on the buried passivation layer of the substrate, wherein
 - a first field plate is defined in the first metallization region in the area between the isolating layer and the slightly doped zone of the component, and
 - a second field plate is defined in the second metallization region in the area of the slightly doped zone of the component.
12. (New) An SOI device as claimed in Claim 11, wherein the lateral transistor is a bipolar pnp transistor, and its slightly doped zone is formed by the n-doped region of the pnp transistor.
13. (New) An SOI device as claimed in Claim 11, wherein the first field plate is embedded in an oxide-based, first passivation layer.
14. (New) An SOI device as claimed in Claim 12, wherein the first field plate is embedded in an oxide-based, first passivation layer.
15. (New) An SOI device as claimed in Claim 12, wherein the pnp transistor is part of an integrated circuit.

16. (New) A method of manufacturing a semiconductor device, wherein:

at least one component having at least one slightly doped zone is integrated in a silicon substrate that is provided with a buried oxide-based passivation layer;

at least a first, in particular planar, metallization region is arranged between the isolating layer and the component,

at least one isolating layer made of a dielectric material is provided onto the silicon substrate using, in particular, adhesive means, so as to transfer the SOI-device onto the isolating layer, and

a second, in particular planar, metallization region is provided on the side of the silicon substrate facing away from the isolating layer, in the area of the component, on the oxide-based buried passivation layer of the substrate, wherein

the component is a lateral transistor;

a first field plate is defined in the first metallization region in the area between the isolating layer and the slightly doped zone of the component, and

a second field plate is defined in the second metallization region in the area of the slightly doped zone of the component.